



Inorganic cesium lead halide CsPbX_3 nanowires for long-term stable solar cells

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ABSTRACT ABX_3 -type organic-inorganic hybrid halide perovskite materials have been recognized as promising candidates for optoelectronic applications. However, poor stability of organic-inorganic hybrid perovskite hinders their forward long-term utilization and hence an effective strategy is needed to replace the organic part with an inorganic cation. Herein, all inorganic CsPbI_3 nanowires with a diameter of 50–100 nm are synthesized on fluorine-doped tin oxide glass via a simple solution-dipping process, which are further transformed into CsPbBr_3 nanowires through a solution-phase halide exchange method. A phase change from non-perovskite to perovskite structure is observed during the ion substitution process of I^- by Br^- , which is elaborated by X-ray diffraction, absorption and photoluminescence spectra. We for the first time apply the as-formed CsPbI_3 and CsPbBr_3 nanowires into perovskite solar cells, yielding power conversion efficiency of 0.11% and 1.21%, respectively. The inorganic CsPbBr_3 nanowire solar cell shows impressive stability which still remains 99% of the initial power conversion efficiency even after 5500 h aging.

Keywords: inorganic perovskite, nanowires, ion exchange, solar cells, long-term stability

INTRODUCTION

The past seven years have witnessed the rapid development of perovskite solar cells (PSCs), with the power conversion efficiency (PCE) rocketing to 22.1% [1] from the initial 3.8% [2], which strongly demonstrates that organic-inorganic hybrid halide perovskite (hybrid perovskite) is a family of promising materials for optoelectronic applications. Hybrid perovskites have been confirmed to possess numerous highly-appreciated properties, such as prominent sunlight absorption [3], long electron/hole diffusion lengths [4,5], ease and low cost fabrication [6], etc., which

render them an ideal candidate for various applications in light-emitting devices (LEDs) [7], semiconductor laser [8], and photodetectors [9].

However, hybrid perovskites are highly sensitive to moisture [10], ultraviolet (UV) light [11], and heat [12], which hinders their forward application [13,14]. Lead halides are the usual degradation product of the hybrid perovskites [10,15], deteriorating the performance of the solar cells, stemming from the wide bandgap and poor electrical conductivity [16,17]. Fortunately, inorganic perovskites, cesium lead halides (CsPbX_3 , $\text{X}=\text{Cl}$, Br , I) exhibit excellent compositional stability under thermal stress [18], among which CsPbBr_3 possesses an impressive humidity stability [19], showing promise on addressing those issues. Actually, pioneer work has already evidenced that CsPbX_3 ($\text{X}=\text{Br}$, I) perovskites also exhibit significant photoelectric properties. Perovskite CsPbBr_3 is a direct bandgap semiconductor with a bandgap of 2.3 eV [20] and is reported to possess not only a long electron lifetime of 2.5 μs but also a high electron mobility up to $\sim 1000 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$ [21], which far outweighs that of single crystals of MAPbI_3 ($24 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$) [5]. Moreover, of particular note is that cesium halide perovskites greatly outperform hybrid perovskites in terms of stability. It has been demonstrated that PSCs based on CsPbBr_3 are more resistant to humidity and light illumination in comparison with MAPbBr_3 [19]. As for CsPbI_3 , the undesirable yellow phase (non-perovskite structure) is formed under ambient temperature [22] which shows only 0.09% in PCE due to an unfavorable wide bandgap [23].

Morphology control has been investigated to have significant effects on the photophysical and photochemical properties and it is highly recommended as a starting point to enhance the performance of the materials for optoelec-

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tronic applications [24]. For instance, hybrid perovskites in the form of nanowires have been already synthesized and applied into PSCs [25], LEDs [26], laser [27] and photodetectors [28] etc., on account of the prominent properties of nanowires, such as fast electron transportation [29], direct charge transfer pathway [30] and low charge recombination [31]. However, limited attempts have been devoted to the controllable synthesis of all inorganic halide perovskites with well-defined nanostructure. Very recently, one dimensional CsPbX_3 ($X=\text{I}, \text{Br}, \text{Cl}$) nanowires [32] and quasi 2D nanoplates [33] were synthesized respectively by modifying the hot-injection technique reported by Protesescu *et al.* [34], where the as-formed CsPbX_3 nanowires reveal temperature-dependent photoluminescence (PL) and the nanoplates present high photoluminescent quantum yields (PLQYs) up to 90%, both of which are deemed as ideal candidates for optoelectronic devices. However, it is well known that hot-injection technique requires rigorous experimental condition (high temperature, inert atmosphere) and the organic surfactant (oleic acid, oleylamine) bound to the surface is adverse to the charge carrier transportation [35,36], which leads to a foregoing purification step to remove such ligands before film fabrication. Moreover, it is still challenging to employ colloidal solution with specific morphology to assemble film on conductive substrate as a result of dissolution [35] and aggregation [37]. For this reason, it is of great significance to *in situ* synthesize all inorganic CsPbX_3 nanowires on conductive substrate directly without the assistance of organic surfactant.

Herein, we report the synthesis of CsPbI_3 and CsPbBr_3 nanowires on fluorine-doped tin oxide (FTO) glasses by a simple solution-dipping process and solution-phase halide exchange method, respectively. Scanning electron microscopy (SEM), X-ray diffraction spectra (XRD), absorption spectra (UV-vis) and PL spectra were used to investigate the conversion process from CsPbI_3 to CsPbBr_3 nanowires. It is interesting to note such exchange by dipping the CsPbI_3 nanowires/FTO glass into the methanol solution of CsBr and annealing at 150°C can not only induce the exchange of I^- to Br^- , but also result in the structure transformation from nonperovskite structure CsPbI_3 to perovskite structure CsPbBr_3 . After the complete anion exchange of I^- to Br^- , the photovoltaic performance of the planar PSCs based on CsPbBr_3 nanowires is 10 times higher than that of CsPbI_3 nanowires. Furthermore, the current inorganic CsPbBr_3 nanowire solar cell shows excellent stability which remains 99% of the initial PCE even after 5500 h aging time at room temperature.

EXPERIMENTAL SECTION

Materials

Lead iodide (PbI_2 , $\geq 98\%$), lead bromide (PbBr_2 , $\geq 98\%$), 2, 2', 7, 7'-tetrakis-(*N*, *N*-di-*p*-methoxyphenylamine)-9, 9'-spirobifluorene (spiro-OMeTAD), bis(trifluoromethane) sulfonamide lithium salt (Li-TFSi), 4-*tert*-butylpyridine (*t*-BP), chlorobenzene and dimethylformamide (DMF, anhydrous, 99.8%) were purchased from Sigma-Aldrich. Cesium bromide (CsBr , $>99.9\%$), cesium iodide (CsI , $>99.9\%$) and hydroiodic acid (HI , 57% *w/w*) were purchased from Aladdin. Dried methanol and ethanol were purchased from Guangzhou Chemical Reagent factory.

Synthesis of HPbI_3

HPbI_3 powders were synthesized according to a previously reported method [38] by dissolving PbI_2 (9.26 g, 20 mmol) and 57% *w/w* hydroiodic acid (4 mL, 30 mmol) into 30 mL DMF with stirring at room temperature for 2 h. The solvent was removed by evaporating the resulting solution at 60°C , and the precipitate was washed with excess ethanol before dried under vacuum for 24 h.

Synthesis of CsPbI_3 nanowires and CsPbBr_3 nanowires

Forty microliter of HPbI_3 precursor solution (1 mol L^{-1} dissolved in DMF) was firstly deposited onto FTO substrate by spin-coating at 5000 rpm for 60 s. This substrate was then dipped into a solution of 10 mg mL^{-1} CsI in methanol to form yellow CsPbI_3 nanowires. Subsequently, the CsPbI_3 nanowires film grown on FTO glass was dipped into a methanol solution of 10 mg mL^{-1} CsBr for different periods and then annealed at 150°C for 10 min. Here, all the CsPbX_3 ($X=\text{Br}, \text{I}$) samples were annealed at 150°C for 10 min except special explanation.

Fabrication of perovskite solar cells

FTO glasses were pre-patterned with 3 mol L^{-1} HCl and zinc powder before cleaned with deionized water, alcohol, and acetone successively via ultrasonic process. A compact TiO_2 layer was deposited on the FTO glass by spin-coating a colloidal TiO_2 solution at 3000 rpm for 30 s and 5000 rpm for 60 s before annealed at 500°C for 1 h. The TiO_2 colloid solution was prepared following our previous report [39]. After cooling down to room temperature, the compact TiO_2 film was immersed into 0.04 mol L^{-1} TiCl_4 aqueous solution for 30 min at 70°C and then heated to 500°C for 30 min. And then an HPbI_3 layer was prepared on the TiO_2 coated FTO by spin-coating. CsPbI_3 nanowires were obtained by

immersing the as-prepared HPbI₃ film into 10 mg mL⁻¹ CsI methanol solution for 1 min and then annealed at 150°C for 10 min. As for CsPbBr₃ nanowire, the halide exchange was performed by dipping the CsPbI₃ nanowires film into 10 mg mL⁻¹ CsBr solution in methanol for 5 min and then annealed at 150°C for 10 min. Then a hole-transport material solution consisting of spiro-OMeTAD (73.2 mg), Li-TFSi (9.1 mg) and *t*-BP (28.8 μL) and chlorobenzene (1 mL) was spin-coated onto the perovskite nanowires at 5000 rpm for 60 s. An Au layer with a thickness of 100 nm was deposited by magnetron sputtering.

Characterizations

The XRD patterns were recorded on RigakuCo. X-ray powder diffractometer (Cu Kα radiation, λ=1.5418 Å). A UV-vis-NIR spectrophotometer (Shimadzu UV-3600) was employed to measure the UV-vis absorption spectra. The morphology and composition of the samples were measured using a scanning electron microscope (SU8010) and an energy dispersive X-ray detector (IXRF), respectively. PL (excitation at 325 nm) was measured with Edinburgh Instruments LTD (FLSP980). The photovoltaic performance of PSCs was recorded using Keithley 2400 source meter with a scan rate of 0.15 V s⁻¹ under one sun AM 1.5G (100 mW cm⁻²) illumination with a solar light simulator (Oriel, Model:91192) which was calibrated with an NREL standard Si solar cell. And the active area of the cell was defined as 0.16 cm².

RESULTS AND DISCUSSIONS

Synthesis of CsPbI₃ nanowires

A simple and facile solution-dipping method was developed to synthesize the CsPbI₃ nanowires on FTO glass substrate. As schemed in Fig. 1a, the HPbI₃ solution was spin-coated onto the FTO substrate first, followed by dipping into CsI methanol solution to assemble CsPbI₃ nanowires film. The HPbI₃ precursor was synthesized via the reaction of PbI₂ and HI according to the previous report [38]. The XRD pattern (Fig. S1) shows that the peak of PbI₂ at 12.7° shifts to 11.5° after reaction with HI as a result of an increased interlayer distance [38], and the atomic ratio of I to Pb is about 3:1 determined by energy dispersive X-ray spectra (EDX, Table S1), further indicating the successful synthesis of HPbI₃. Fig. 1b shows the morphology of the HPbI₃ film, which is constituted by discontinuous, large sized grains and this phenomenon was also found in a recent report [40]. After reaction with CsI, the parent HPbI₃ film turned yellow, and surprisingly, nanowires with diameters of 50–100 nm and lengths up to several micrometers tightly covered on the FTO glass could be observed (Fig. 1c and Fig. S2a). The XRD patterns of the products can be assigned to orthogonal phase CsPbI₃ (Fig. 2), with a non-perovskite structure (JCPDS Card No. 74-1970) [32].

Importance of HPbI₃ precursor in synthesis of CsPbI₃ nanowires

It should be noted that the HPbI₃ precursor played a vital

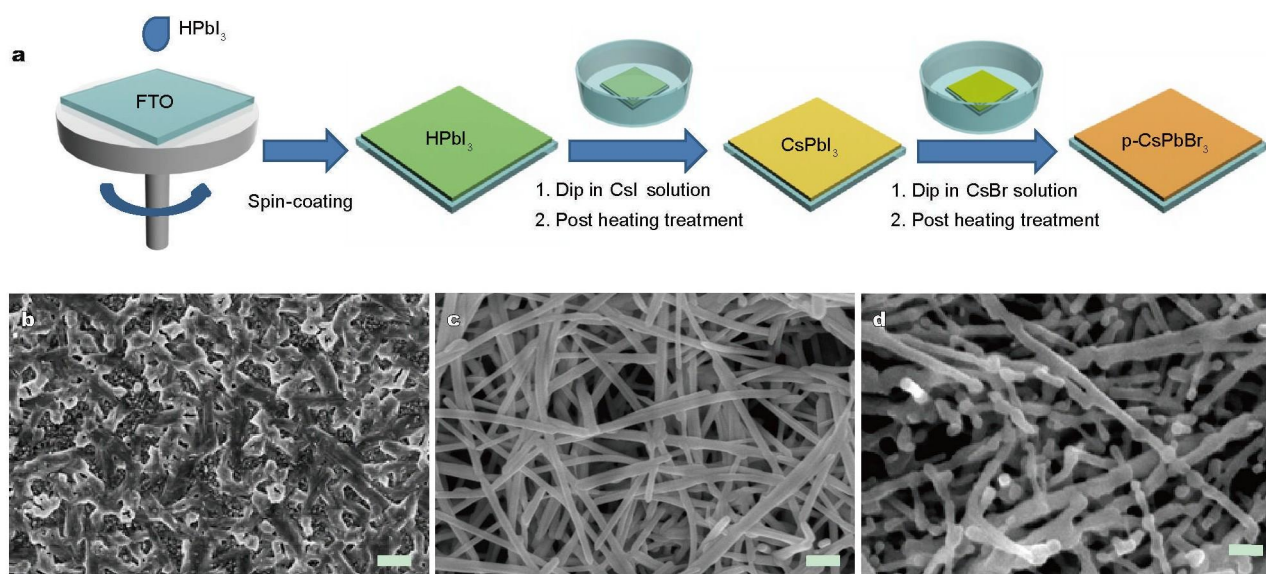


Figure 1 (a) Schematic illustration of the synthesis of CsPbX₃ nanowires, and SEM images of (b) HPbI₃ films, (c) CsPbI₃ nanowires film, and (d) CsPbBr₃ nanowires film. Scale bars are 200 nm. The prefix p represents a perovskite structure.

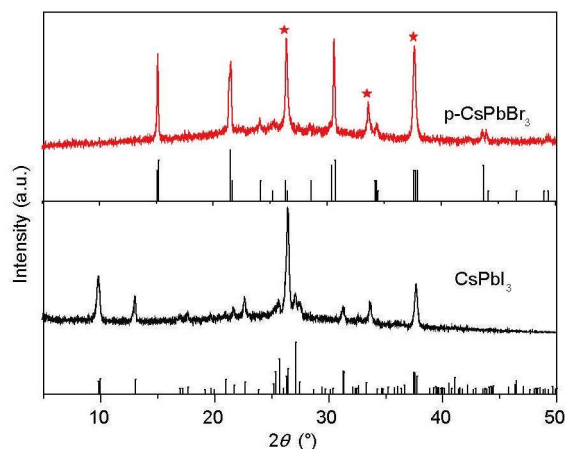


Figure 2 XRD patterns of the as-formed CsPbI₃ nanowires by solution-dipping method and CsPbBr₃ obtained by halide exchange in comparison with standard XRD pattern. Peaks marked with an asterisk are XRD signals assigned to the FTO substrate.

role in the synthesis of CsPbI₃ nanowires. Attempt using the typical PbI₂ precursor film was conducted by dipping into CsI methanol solution. However, the XRD patterns (Fig. S3a) show that the peak of PbI₂ at 12.7° is still clearly observed after a long dipping time even though morphology of the obtained nanowires (Fig. S3b) indicates the incomplete conversion. In contrast, the reaction of HPbI₃ with CsI was astonishingly fast. CsPbI₃ was formed within 5 s and the XRD peak of HPbI₃ disappeared (Fig. S3c). Here, HPbI₃ having a faster complete reaction with CsI could be attributed to an increased layer lattice, which facilitated the reaction with CsI to form CsPbI₃ [38,40].

Synthesis of CsPbBr₃ nanowires via halide exchange

As mentioned above, nonperovskite CsPbI₃ is not beneficial for fabricating PSCs and it requires a high temperature (335°C) to convert to the black phase, which will revert to yellow phase after cooling down at ambient temperature [22]. Concerning that perovskite CsPbBr₃ possesses a superior stability than CsPbI₃ in ambient atmosphere, thus we look forward to converting the CsPbI₃ to CsPbBr₃ with the nanowires morphology maintained. The halide exchange process was performed by exposing the as-formed CsPbI₃ nanowires film into CsBr methanol solution and then annealed at 150°C for 10 min (Fig. 1a).

The accomplishment of the anion substitution of I⁻ by Br⁻ was accompanied by the color of the film turning to orange (CsPbBr₃) from the inchoative pale yellow of CsPbI₃. The XRD patterns in Fig. 2 confirm the formation of orthogonal phase CsPbBr₃, with a perovskite structure

(JCPDS Card No. 72-7929) [19,32]. Highlighted in Fig. 1d and Fig. S2b, the CsPbBr₃ nanowires were successfully synthesized by anion exchange, with diameters merely changed to 50–200 nm. Compared with the CsPbI₃, the CsPbBr₃ nanowires showed an uneven diameter and a rougher surface. The slight morphology variation is probably attributed to the crystal structural change from nonperovskite to perovskite structure during the halide exchange of I⁻ by Br⁻. The PbI₆ octahedra are isolated in the nonperovskite CsPbI₃, while PbBr₆ octahedra are connected in the perovskite CsPbBr₃ structure, which will be further discussed below. Cross-sectional SEM images (Fig. S4) illustrate the thickness variation between the as-prepared materials. The thickness of HPbI₃ film on FTO glass is ca. 300 nm (Fig. S4a), while after reaction with CsI, the thickness was almost doubled (Fig. S4b). Nevertheless, the thickness no longer changes during the Br substitution process (Fig. S4c).

The advent of ion substitution was proposed to figure out the difficulties in direct synthesis of materials with a specific morphology [41]. Here, an expectation of direct synthesis of CsPbBr₃ nanowires on FTO glass substrate was terminated by the trial of dipping the HPbI₃ film/FTO into a CsBr methanol solution straightly. XRD patterns (Fig. S5a) evidence the formation of perovskite structure CsPbBr₃ after dipping for 5 min, while the SEM image, presented in Fig. S5b indicates the morphology of cubes with a diameter of hundreds of nanometer was acquired instead of nanowires, which underlines the necessity of sacrificing the CsPbI₃ nanowires as templates for the sake of CsPbBr₃ nanowires.

Studies of anion exchange via XRD, UV-vis and PL

Anion exchange in cesium lead halide perovskite nanocrystals [42,43] has been demonstrated, while it has been rarely studied in bulk films [37]. To further gain insight into the ion exchange dynamics of the conversion reaction from CsPbI₃ to CsPbBr₃, XRD patterns of the CsPbI₃ nanowires film as a function of dipping time into CsBr solution were measured. Fig. 3a indicates that, at the initial 20 s, no emerging XRD signals was detected, implying a similar crystallographic structure of nonperovskite CsPbI₃ was maintained but a magnification of XRD patterns (Fig. S6) showed that the XRD peaks of CsPbI₃ located at 9.9° and 13.1° were gradually shifted to higher angles at 10.1° and 13.3° with increasing dipping time respectively, indicating that I substituted by smaller atom Br and nonperovskite CsPbI_{3-x}Br_x was formed within such a short dipping time.

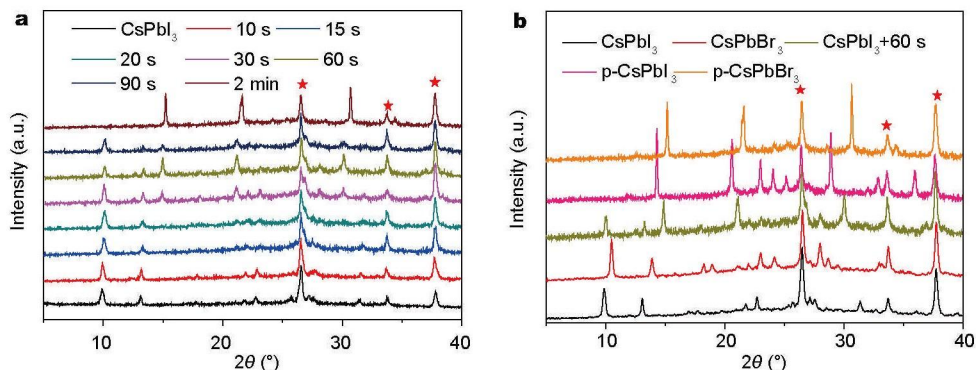


Figure 3 (a) XRD pattern of CsPbI₃ nanowires film dipped in CsBr solution for varying time. (b) XRD pattern of the sample with dipping time of 60 s was compared with that of nonperovskite and perovskite CsPbI₃ and CsPbBr₃. Peak marked with an asterisk are XRD signals assigned to FTO substrate.

Extending the dipping time to 30 s till 90 s, several distinct emerging peaks at 14.9°, 21.1° and 30.1° could be easily observed. A further analysis by comparing CsBr solution for 60 s with that of both perovskite structure CsPbX₃ (X=I, Br) and nonperovskite structure CsPbX₃ (X=I, Br; Fig. 3b) suggested both two phases of CsPbI_{3-x}Br_x (perovskite structure and nonperovskite structure) coexisted since the XRD peaks of intermediate product stood at the middle of the corresponding peaks of CsPbI₃ and CsPbBr₃. Whereafter, with dipping time increased to 2 min, a pure orthorhombic perovskite CsPbBr₃ was obtained, characterized with XRD patterns (Fig. 2) [19, 35]. Further prolonging the dipping time (e.g., >2 min) did not show any difference in XRD patterns (Fig. S7a), indicating the complete conversion of I⁻ to Br⁻.

In order to explore the exact role of the post heat treatment in the aforementioned halide exchange process, we also measured XRD patterns of CsPbI₃ dipped in CsBr solution for varying time but without a post thermal treatment (Fig. S8a). The magnified of XRD patterns (Fig. S8b), reveal that the XRD signals of CsPbI₃ at 9.9° and 13.1° shifted to higher angles of 10.4° and 13.8° respectively after exposed to CsBr solution for 2 min, and no variations appeared to the XRD patterns as dipping process continued (Fig. S8c). Whereas, after the complete conversion, the color of the CsPbI₃ film turned from the initial yellow to white and the XRD patterns of the final white product can be assigned as orthorhombic CsPbBr₃ with a nonperovskite structure (Fig. S8d, JCPDS Card No. 74-2251), which is different from the results obtained by the halide process including a post heat treatment schemed in Fig. 1a. In addition, no XRD peaks of perovskite structure CsPbX₃ could be found during the ion substitution without a post heat treatment process (Fig. S8a), suggesting that the post

heat treatment was necessary to form the perovskite structure CsPbX₃. In other words, the nonperovskite CsPbI₃ was transferred into the nonperovskite CsPbBr₃ after dipped into CsBr solution for 2 min, and a following post heat treatment (annealing at 150°C for 10 min) enabled the phase change from nonperovskite CsPbBr₃ to perovskite structure CsPbBr₃, which was further proved by the temperature dependence XRD patterns of the as-formed nonperovskite structure CsPbBr₃ (Fig. S9). There is no variation in the XRD patterns until the temperature was raised to 150°C, and then the XRD peaks of perovskite CsPbBr₃ appeared while that of nonperovskite CsPbBr₃ disappeared.

As schemed in Fig. 4, we can make a conclusion for the halide exchange process including a post heat treatment, that nonperovskite CsPbI_{3-x}Br_x was formed within 30 s; both two phases of CsPbI_{3-x}Br_x (nonperovskite structure and perovskite structure) coexisted during 30–90 s; after 2 min the full conversion from CsPbI₃ to CsPbBr₃ was achieved with a phase change from initial nonperovskite to perovskite structure.

Transformation in crystal structure is always accompanied with photophysical properties variation [44]. In this regard, the absorption spectra of the CsPbI₃ nanowires films as a function of dipping time into CsBr methanol solution were characterized (Fig. 5a). The absorption onset of solution-phase synthesized CsPbI₃ nanowires locates at 449 nm with a bandgap of 2.78 eV from Tauc plot (Fig. S10), which matches well with the previous report [19]. After ion substitution completed, the as-formed CsPbBr₃ perovskite exhibited an absorption onset at 540 nm with a band gap of 2.30 eV. The rightmost blue solid line in Fig. 5a represents the absorption spectra of perovskite structure CsPbI₃ (obtained by heating the as-formed CsPbI₃ nano-

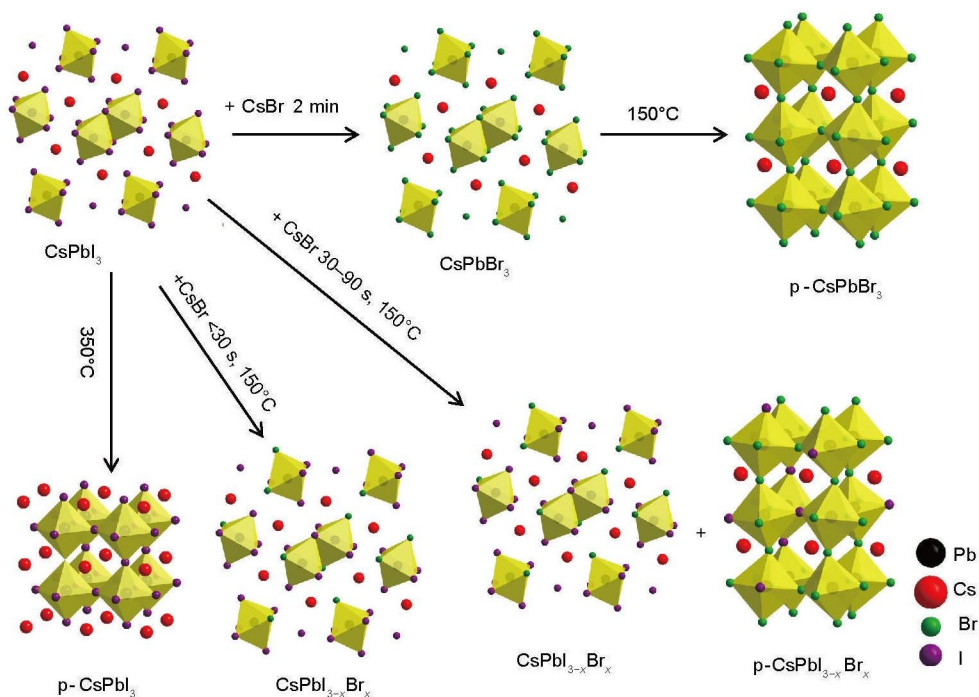


Figure 4 The schematic diagram of structure conversion from nonperovskite CsPbI_3 to perovskite CsPbBr_3 .

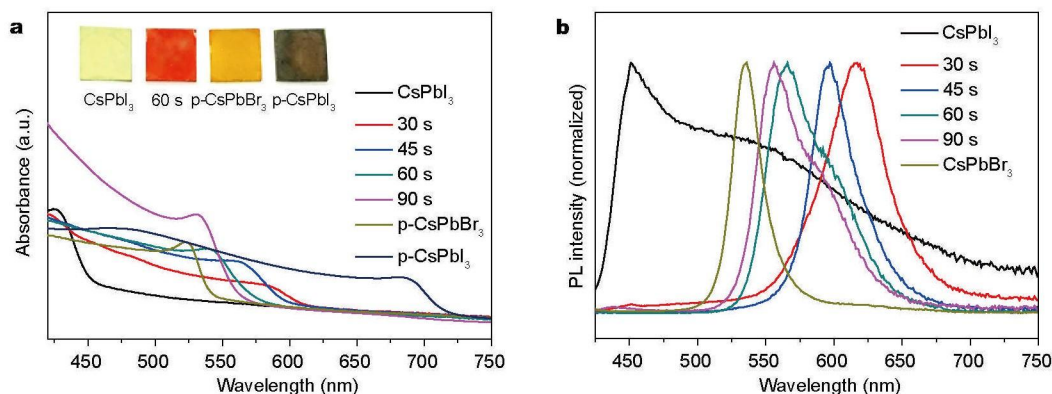


Figure 5 (a) Absorption spectra and (b) normalized PL spectra of CsPbI_3 nanowires films dipped in CsBr solution for varying time. The inset photographs are CsPbI_3 , CsPbI_3 film with dipping time of 60 s, p-CsPbBr_3 and p-CsPbI_3 films from left to right, respectively.

wires film at 350°C) with an absorption onset at 700 nm and a bandgap of 1.7 eV (Fig. S10). It is interesting to note that the halide-exchange intermediate products (dipping time from 30 to 90 s) possess a wider absorption range than the initial material CsPbI_3 and the final product CsPbBr_3 . More specifically, after dipped in CsBr solution for 30 s, the absorption onset of the CsPbI_3 film shifts to around 615 nm, and towards to 600 nm (for 45 s), 581 nm (for 60 s) and 570 nm (for 90 s) gradually as I^- substitution continued, and finally towards the onset of CsPbBr_3 540 nm with the shift ceased as dipping time advances (Fig. S7b). Studies about CsPbX_3 nanocrystals halide exchange have illustrated that

the absorption onset of the perovskite structure $\text{CsPbI}_{3-x}\text{Br}_x$ can be varied from 520–700 nm by adjusting the atom ratio of Br to I [42,43], and therefore it can be concluded that the perovskite structure $\text{CsPbI}_{3-x}\text{Br}_x$ intermediate was formed, which is consistent with the aforementioned XRD analysis in Fig. 3b. The inset photographs in Fig. 5a display the color variation of the as-prepared CsPbI_3 nanowires film after dipping into CsBr solution or heat treatment. The pale yellow film was the as-prepared CsPbI_3 nanowires, and after dipped into CsBr solution for 60 s, the film was red as a result of the formation of perovskite $\text{CsPbI}_{3-x}\text{Br}_x$ but the final product perovskite CsPbBr_3 nanowires was or-

ange and the black film was the perovskite CsPbI₃ film. The above analysis demonstrated that perovskite structure CsPbI_{3-x}Br_x with a tunable bandgap can be formed via a careful control of the dipping time.

Corresponding to UV-vis, PL spectra also witnessed such interesting phenomenon in optical spectrum, as shown in Fig. 5b. The PL spectrum of the as-prepared CsPbI₃ nanowires consists of two peaks centered at 450 and 540 nm. The narrow peak is assigned as the band edge emission while the broad peak has been previously attributed to the formation of self-trapped excitons [32]. The temperature-dependent PL spectra of CsPbI₃ NWs in Fig. S11 reveal that the exciton emission peak of CsPbI₃ red-shifts with increasing temperature from 100 to 298 K, which is consistent with the formation of self-trapped exciton which can produce strong electron-phonon coupling contribution to dictate band gap behavior [32]. Similar to the UV-vis spectra, as dipping time extending from 30 to 90 s, the PL peaks shift from 620 to 560 nm. The PL emission peak of the final product is located at 538 nm indicating the as-formed CsPbBr₃ nanowires are PL active, with a narrow full-width of half maximum (FWHM) about 40 nm. Further prolonging the dipping time to more than 2 min, no differences between the PL peaks position are observed, indicating full halide exchange from CsPbI₃ to CsPbBr₃ (Fig. S7c).

Photovoltaic performance of PSCs based on CsPbX₃ nanowires

The optoelectronic application of perovskite material is becoming a recent research hotspot. In this regard, the current *in-situ* growth of CsPbI₃ and CsPbBr₃ nanowires are further applied to the PSCs. To elucidate that such method has a favorable reproducibility, ten independent devices based on CsPbI₃ and CsPbBr₃ nanowires were measured, respectively (as shown in Fig. S12). Fig. 6a shows the current density-voltage curves of both solar cells based on CsPbI₃ and CsPbBr₃ nanowires. As listed in Table 1, the performance of device based on CsPbI₃ yields a short circuit current density (*J*_{sc}) of 0.415 mA cm⁻², an open circuit voltage (*V*_{oc}) of 643 mV, a fill factor (FF) of 0.429, and a PCE of 0.11%. By contrast, the device based on CsPbBr₃ nanowires formed by anion exchange achieves a *J*_{sc} of 2.96 mA cm⁻², a *V*_{oc} of 851 mV, an FF of 0.445 and a PCE of 1.21%. It is very interesting to note that more than tenfold enhancement in the PCE is achieved by the substitution of I⁻ by Br⁻. The PCE of the devices based on CsPbI_{3-x}Br_x intermediate formed in the conversion process was measured with an inferior performance compared with pure CsPbBr₃, properly owing to the existence of nonperovskite counterpart serving as traps limiting the photovoltaic properties. Fig. 6b presents the cross-sectional SEM image of the device based on CsPbBr₃ nano-

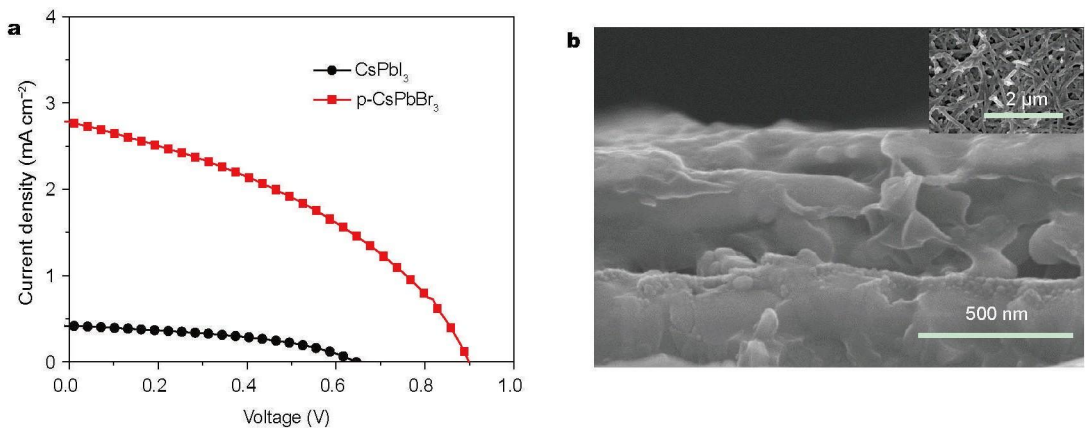


Figure 6 (a) *J*-*V* characteristics of the PSC devices and (b) cross-sectional and plane-view (inset image) SEM images of a full cell based on CsPbBr₃ nanowires.

Table 1 Device parameters of PSCs

	<i>J</i> _{sc} (mA cm ⁻²)	<i>V</i> _{oc} (mV)	PCE (%)	FF
CsPbI ₃ nanowires	0.415	643	0.11	0.429
p-CsPbBr ₃ nanowires	2.96	851	1.21	0.445

wires (FTO glass/TiO₂ compact layer/CsPbBr₃ nanowires/spiro-OMeTAD/Au) while the inset SEM image

in Fig. 6b is the plane-view image of the device based on CsPbBr_3 , where nanowires can be easily seen revealing that spiro-OMeTAD does not form a top layer upon the nanowires film but fills the empty space among nanowires, as does Au electrode. Moreover, there is no distinct layer boundary between the CsPbBr_3 nanowires with spiro-OMeTAD and Au electrode from the cross-sectional SEM image. Therefore, these inferior performances are mainly attributed to the insufficient coverage of the random CsPbX_3 nanowires on the substrate, which causes a direct contact between c-TiO₂ with spiro-OMeTAD or Au electrode resulting in the electron-hole recombination [45]. On the other hand, nanowires with an incomplete coverage on substrate will lead to a great loss in light harvesting, thus a decrease in J_{SC} [46]. For comparison, solar cells based on cube-based CsPbBr_3 films were fabricated with the same configuration. Table S2 summarized the photovoltaic metrics of 8 devices based on cubed-based CsPbBr_3 film with an average PCE of 0.14%, which is lower than that of CsPbBr_3 nanowires. By contrast, the better performance can be attributed to prominent properties of nanowires, such as fast electron transportation and direct charge transfer pathway.

Long-term stability of PSCs based on CsPbX_3 nanowires

The stability of solar cell is a crucial issue for the commercial application. Till today, the long-time stability of organic-inorganic PSC is still unsatisfactory and required to be resolved urgently. Herein, the stability study of the inorganic CsPbI_3 and CsPbBr_3 nanowire planar perovskite solar cell is further performed. Fig. 7 presents the normalized stability curves of both CsPbI_3 and CsPbBr_3 nanowire solar cells, which highlight that the current inorganic perovskite solar cells are highly stable even after around 5500 h aging at ambient condition in dark. Such impressive stability of inorganic perovskite nanowire solar cells will potentially stimulate the wide applications.

CONCLUSIONS

In summary, we reported a simple solution-dipping method and halide exchange technique to synthesize the CsPbI_3 and CsPbBr_3 nanowires grown on FTO glass, respectively. Herein, SEM, XRD patterns, UV-vis spectra and PL spectra studies reveal that the nonperovskite structure CsPbI_3 is transferred into nonperovskite structure $\text{CsPbI}_{3-x}\text{Br}_x$ as the first step of the halide conversion, and then perovskite structure $\text{CsPbI}_{3-x}\text{Br}_x$ appears together be-

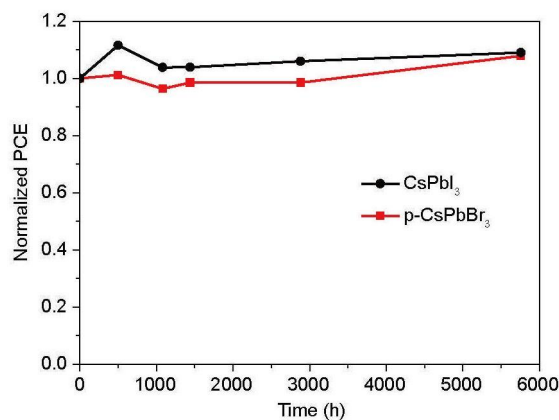


Figure 7 Normalized PCE for devices based on CsPbI_3 and p- CsPbBr_3 nanowires as a function of aging time.

fore the complete conversion to perovskite structural CsPbBr_3 . PSC devices based on CsPbI_3 and CsPbBr_3 nanowires reached a PCE of 0.11% and 1.21%, respectively, and both exhibited impressive stability over 5500 h. Further studies on the thickness optimization of the CsPbX_3 nanowires and inorganic-organic hybrid MAPbX_3 nanowires are expected to obtain both high efficiency and good stability PSCs. Additionally, this work provides a simple solution-phase synthesis method to the *in situ* synthesis of the inorganic perovskite nanowires, which will stimulate the great potentials in semi-transparent perovskite solar cells, photodetectors and other optoelectronics.

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Author contributions Kuang DB and Liao JF designed the experiments. Liao JF performed the material synthesis, measurements, data analysis and prepared the manuscript. Li WG, Rao HS, Chen BX, Wang XD and Chen HY provided helps in the characterizations and revision of the manuscript. All authors contributed to the general discussion.

Conflict of interest The authors declare that they have no conflict of interest.

Supplementary information Experimental details are available in the online version of the paper.



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稳定的无机卤化铅铯纳米线钙钛矿电池

廖金凤, 李文广, 饶华商, 陈白雪, 王旭东, 陈洪燕, 匡代彬*

摘要 有机无机杂化钙钛矿因其优异的光电性能受到广泛关注, 但是其对湿度、热的不稳定性会限制钙钛矿电池的进一步发展. 本文通过简单的溶液浸泡法在导电基底上制备了尺寸为50–100 nm的全无机碘化铅铯纳米线, 并通过离子交换法将碘化铅铯置换成溴化铅铯纳米线. 文章通过X射线衍射谱、紫外可见吸收光谱、荧光发光光谱对I⁻离子交换成Br⁻离子过程进行了研究. 结果发现I-Br离子交换过程中伴随着晶体结构的变化, 起初的碘化铅铯为非钙钛矿结构, 离子交换后制备的溴化铅铯为钙钛矿结构. 本文将全无机卤化铅铯纳米线应用在钙钛矿电池器件中, 器件显示出优越的稳定性, 放置5500小时效率几乎未衰减.

Supplementary Information

Inorganic cesium lead halide CsPbX_3 nanowires for long-term stable solar cells

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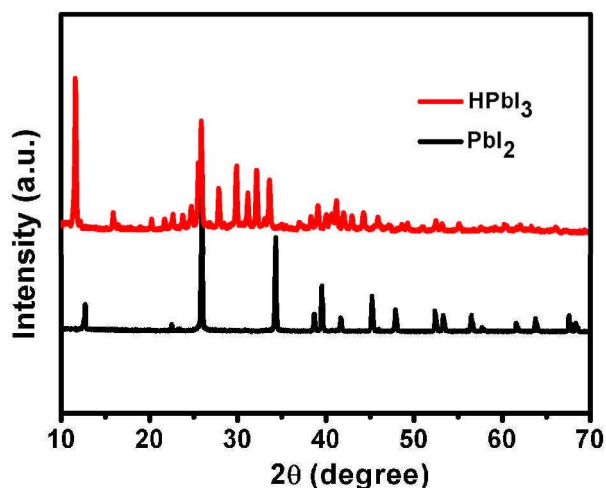


Figure S1 XRD patterns of HPbI_3 and PbI_2 powder.

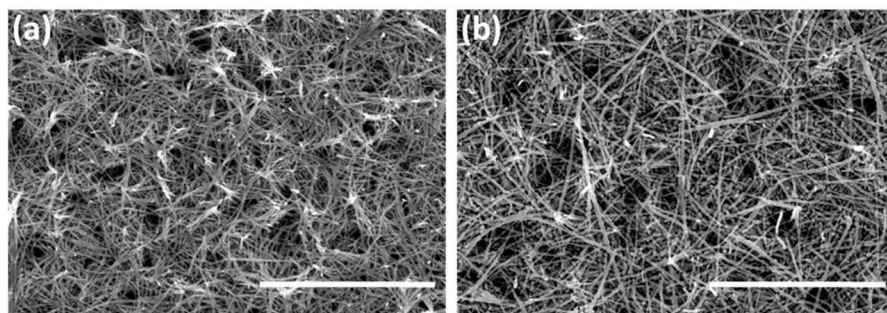


Figure S2 Plane-view SEM images of (a) CsPbI_3 nanowires film prepared by precursor HPbI_3 and (b) CsPbBr_3 nanowires film prepared by halide exchange of CsPbI_3 nanowires. Scale bars are 5 μm .

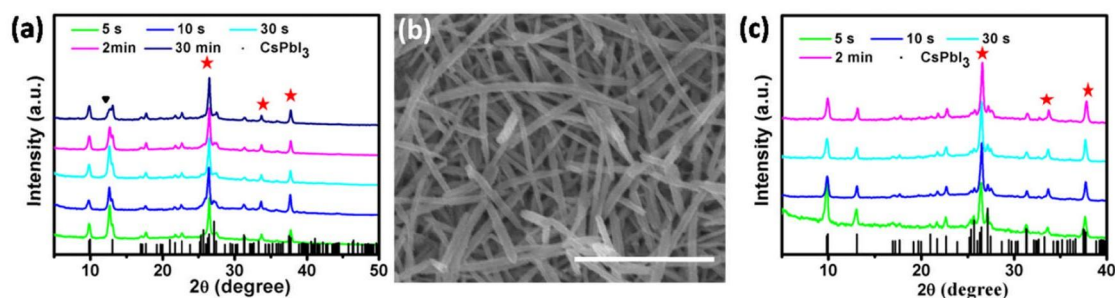


Figure S3 (a) XRD patterns of PbI₂ films and (c) HPbI₃ films dipped into CsI solution for varying time compared with the standard pattern of CsPbI₃. Peaks marked with an asterisk are XRD signals assigned to FTO substrate while marked with inverted triangle is XRD signal of PbI₂. (b) SEM image of PbI₂ film after dipped into CsI methanol solution. Scale bar is 1 μm.

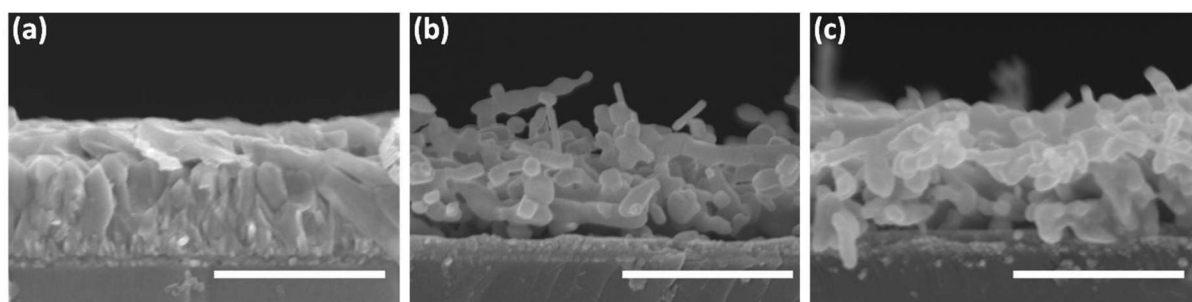


Figure S4 Cross-sectional SEM images of (a) HPbI₃ film, (b) CsPbI₃ nanowires film and (c) CsPbBr₃ nanowires film. Scale bars are 1 μm.

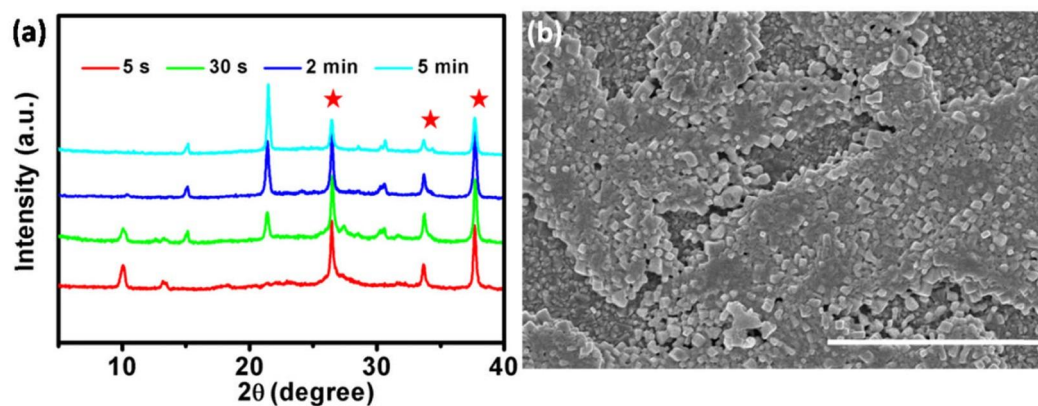


Figure S5 (a) XRD patterns of HPbI₃ films dipping into CsBr solution for varying time and (b) SEM image for the sample dipped for 2 min. Peaks marked with an asterisk are XRD signals assigned to FTO substrate. Scale bar is 5 μm.

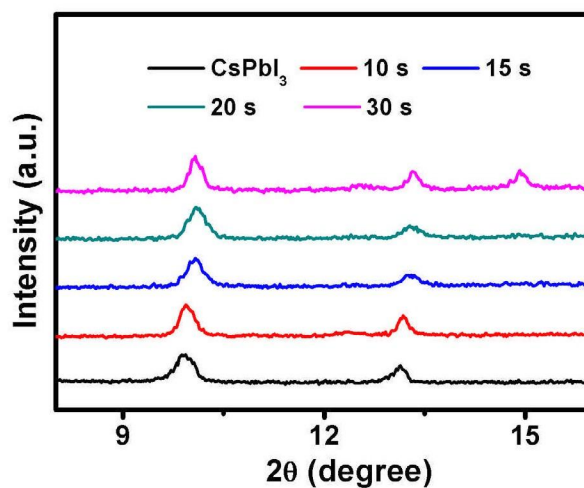


Figure S6 The magnification XRD patterns for CsPbI₃ nanowires film dipping time within 30 s.

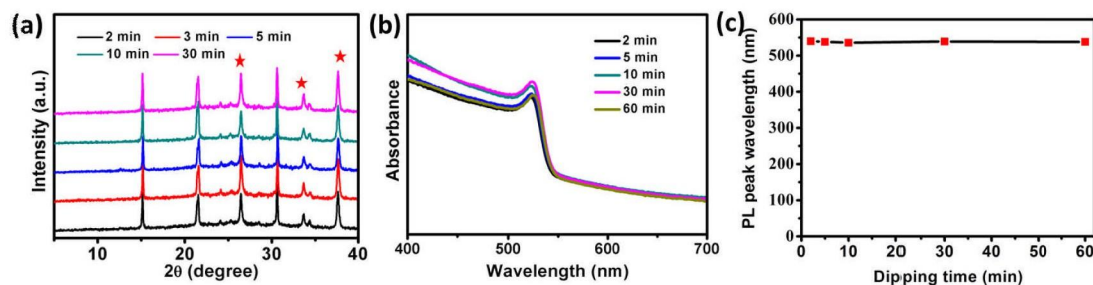


Figure S7 (a) XRD patterns, (b) UV-vis spectra and (c) PL speak wavelength of CsPbI₃ nanowires films dipped into CsBr methanol solution for a longer time (≥ 2 min) and annealed at 150 °C. Peaks marked with an asterisk are XRD signals assigned to FTO substrate.

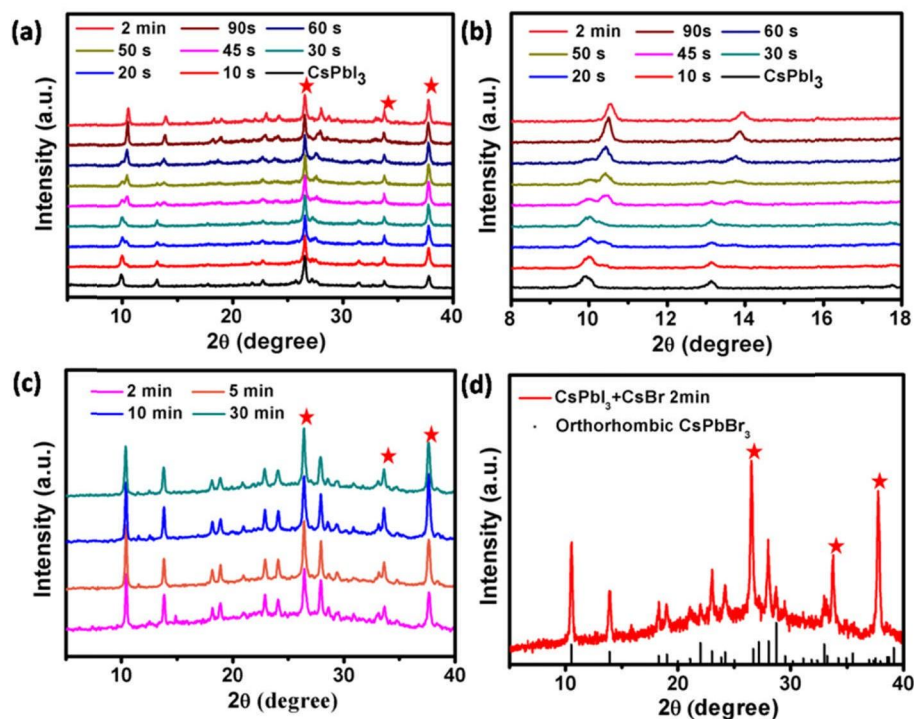


Figure S8 XRD patterns of (a) CsPbI₃ nanowires films dipped in CsBr solution for varying time without thermal treatment. (b) The magnification XRD patterns of a. (c) XRD patterns for CsPbI₃ nanowires films dipped into CsBr methanol solution for a longer time (≥ 2 min). (d) XRD pattern of CsPbI₃ nanowires film dipped in CsBr solution for 2 min compared with the standard XRD patterns of the nonperovskite CsPbBr₃. Peaks marked with an asterisk are XRD signals assigned to FTO substrate.

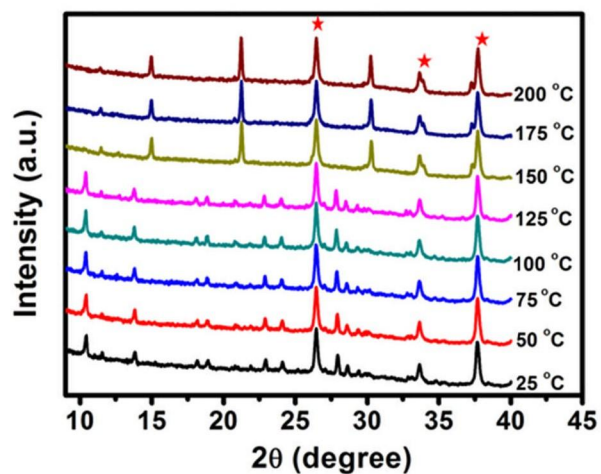


Figure S9 Temperature dependence XRD patterns of the as-formed nonperovskite CsPbBr₃. Peaks marked with an asterisk are XRD signals assigned to FTO substrate.

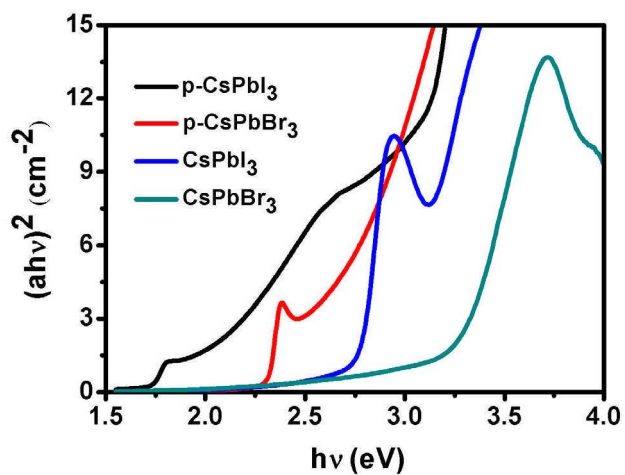


Figure S10 Tauc plots of CsPbI₃ and CsPbBr₃ with both non-perovskite and perovskite structure. (The prefix p presents a perovskite structure).

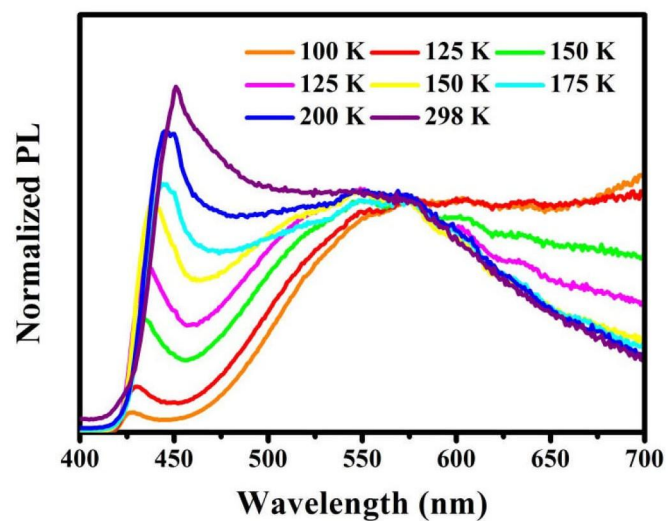


Figure S11 Temperature-dependent PL spectra of CsPbI₃ nanowires.

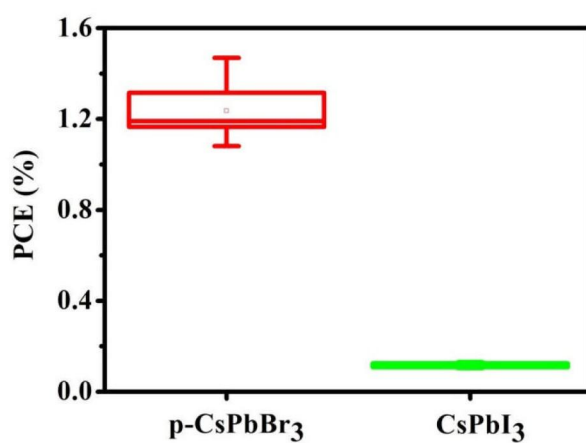


Figure S12 The box-chart image of power conversion efficiency for 10 devices based on p-CsPbBr₃ and CsPbI₃. (The prefix p presents a perovskite structure).

Table S1 Elemental analysis by energy dispersive X-ray spectra (EDX) for HPbI₃ powder

Element	Weight%	Atomic%
O K	5.20	12.73
I L	44.09	13.61
Pb M	25.16	4.76
Totals	100.00	

Table S2 Photovoltaic metrics of 8 devices based on cubed based CsPbBr₃ film

No.	V_{OC} (V)	J_{SC} (mA cm ⁻²)	FF	PCE (%)
1	535	0.75	0.361	0.144
2	555	0.83	0.370	0.171
3	439	0.96	0.358	0.151
4	451	0.71	0.373	0.119
5	578	0.68	0.368	0.145
6	428	0.75	0.323	0.104
7	541	0.69	0.452	0.170
8	537	0.62	0.461	0.152
Average	508	0.75	0.383	0.145